NSN 5962-01-407-8100

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-407-8100

view Offilite at https://aerobasegroup.com/hist//3302-01-407-0100
Body Length:
0.440 inches
Body Width:
Between 0.245 inches and 0.285 inches
Body Height:
Between 0.045 inches and 0.085 inches
Maximum Power Dissipation Rating:
794.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Bipolar and schottky
Inclosure Material:
Silicon
Inclosure Configuration:
Flat pack
Input Circuit Pattern:
10 input
Criticality Code Justification:
Feat
Case Outline Source And Designator:
F-5 mil-m-38510
Current Rating Per Characteristic:
100.00 milliamperes forward current, nonrepetitive, peak total value
Voltage Rating And Type Per Characteristic:
-0.5 volts total supply and 7.0 volts total supply
Time Rating Per Chacteristic:
35.00 nanoseconds propagation delay time, high to low level output and 35.00 nanoseconds propagation delay time, low to high level
output
Memory Device Type:
Prom
Hybrid Technology Type:
Monolithic
Special Features:
Terminal surface treatment is gold or solder or tin
Test Data Document:
81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification

format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain

environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

16 flat leads

Specification Data:

813/0-mil-m-38510/20/ government enecification

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N/a

Unit Of Measure:

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Demilitarization:

No

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